

MOSFETs Silicon N-Channel MOS

# SSM3K324R

#### 1. Applications

- · Power Management Switches
- · DC-DC Converters

#### 2. Features

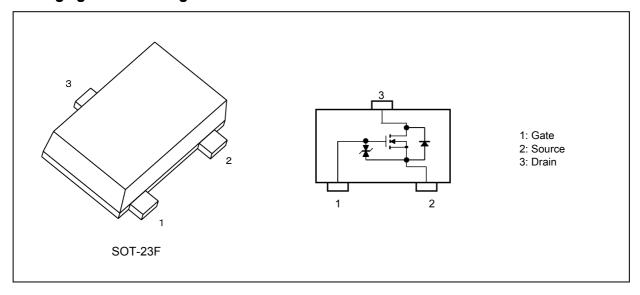
- (1) 1.8-V gate drive voltage.
- (2) Low drain-source on-resistance

: RDS(ON) = 56 m $\Omega$  (max) (@V<sub>GS</sub> = 4.5 V)

 $RDS(ON) = 72 \text{ m}\Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$ 

RDS(ON) = 109 m $\Omega$  (max) (@V<sub>GS</sub> = 1.8 V)

#### 3. Packaging and Pin Assignment





### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				$V_{DSS}$	30	V
Gate-source voltage	,			$V_{GSS}$	± 12	
Drain current (DC)			(Note 1)	Ι <sub>D</sub>	4.0	Α
Drain current (pulsed)	,		(Note 1), (Note 2)	$I_{DP}$	10	
Power dissipation	,		(Note 3)	$P_D$	1	W
Power dissipation	(t	≤ 10 s)	(Note 3)	P <sub>D</sub>	2	
Channel temperature	,			$T_ch$	150	ů
Storage temperature				T <sub>stg</sub>	-50 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	± 10	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	_	_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = -12 V	18	_	_	
Gate threshold voltage	(Note 2)	$V_{th}$	$V_{DS} = 3 \text{ V}, I_{D} = 1 \text{ mA}$	0.4	_	1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 2.0 A, V <sub>GS</sub> = 4.5 V	_	45	56	mΩ
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 2.5 V	_	55	72	
			I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 1.8 V	_	69	109	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_{D} = 2.0 \text{ A}$	_	10.5	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current  $(I_D)$  to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

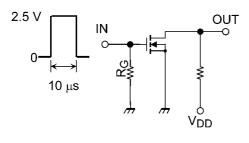
Take this into consideration when using the device.

Note 3: Pulse measurement.

# 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,	_	200	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	13	_	
Output capacitance	C <sub>oss</sub>		_	40	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD} = 10 \text{ V}, I_D = 2.0 \text{ A}$	_	9	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to 2.5 V, $R_{G}$ = 4.7 $\Omega$ See Chapter 5.3.	_	9.5	_	

#### 5.3. Switching Time Test Circuit



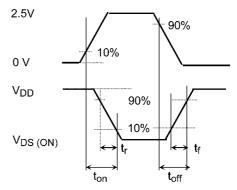


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}$ = 10 V, $V_{GS}$ = 4.5 V,	_	2.2	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = 2.4 A	_	0.5	_	
Gate-drain charge	$Q_{gd}$		_	0.9		



# 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (	Note 1)	V <sub>DSF</sub>	$I_D = -4.0 \text{ A}, V_{GS} = 0 \text{ V}$	_	-0.8	-1.2	V

Note 1: Pulse measurement.

## 6. Marking

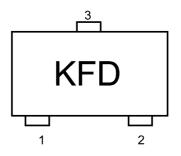


Fig. 6.1 Marking

#### 7. Characteristics Curves (Note)

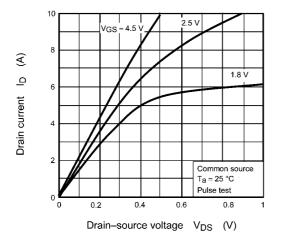


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

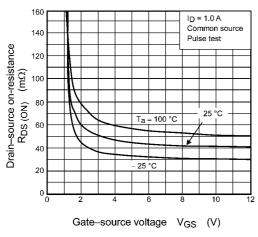


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

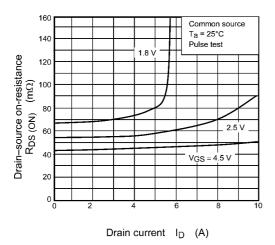


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

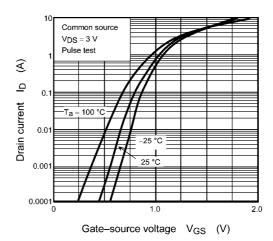


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

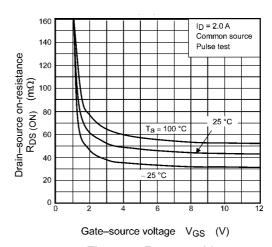


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

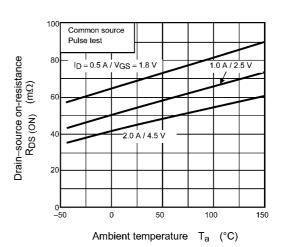


Fig. 7.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

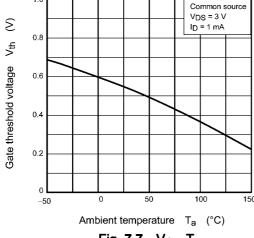


Fig. 7.7 V<sub>th</sub> - T<sub>a</sub>

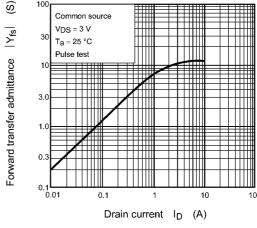


Fig. 7.8 |Yfs| - ID

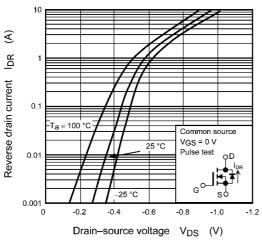


Fig. 7.9 IDR - VDS

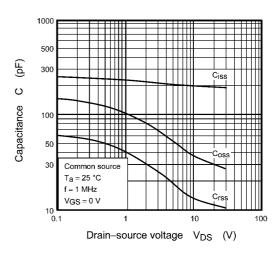


Fig. 7.10 C - V<sub>DS</sub>

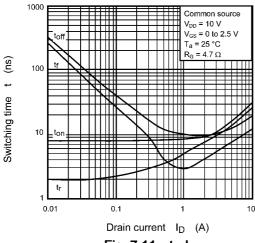


Fig. 7.11 t-I<sub>D</sub>

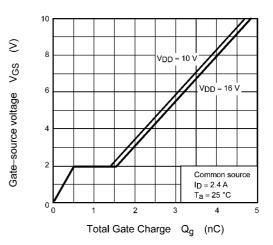
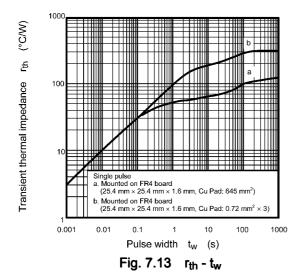
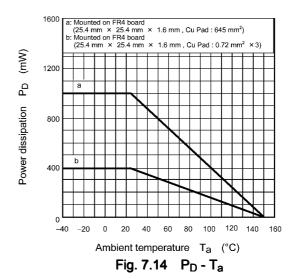


Fig. 7.12 Dynamic Input Characteristics



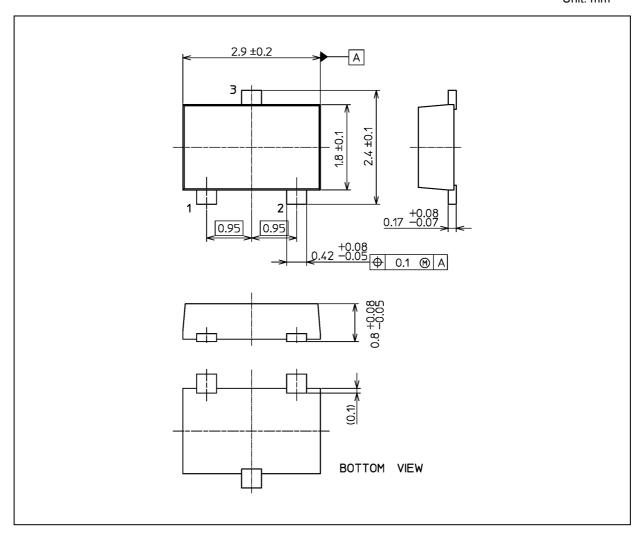


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	

Rev.2.0



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